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Hydrogen in crystalline semiconductors

DOI: 10.1007/bf00615975

Applied Physics A: Solids and Surfaces, 1987, 43, 153-195.

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#	Paper	IF	Citations
897	Hydrogen Injection Into P-Type Silicon By Chemical Etching. <i>Materials Research Society Symposia Proceedings</i> , 1987 , 104, 285		37
896	Passivation of shallow acceptors by H in Si: A microscopic study by perturbed angular correlations. <i>Physical Review Letters</i> , 1987 , 59, 2087-2090	7.4	69
895	Passivation of N-Type Silicon by Hydrogen. <i>Materials Research Society Symposia Proceedings</i> , 1987 , 104, 281		7
894	Hetroepitaxy of GaAs by MBE on High Temperature Hydrogen Annealed Nominally (100) Oriented Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1987 , 102, 443		
893	Hydrogen in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1987 , 104, 229		18
892	Theory of Hydrogen Reactions in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1987 , 104, 253		
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